

2SC3944, 2SC3944A

Silicon NPN epitaxial planar type

For low-frequency driver and high power amplification

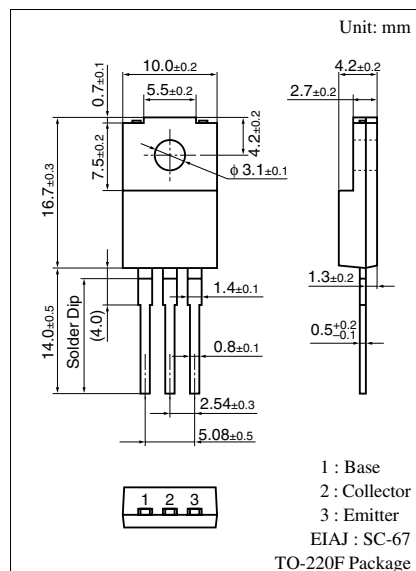
Complementary to 2SA1535 and 2SA1535A

■ Features

- Excellent current I_C characteristics of forward current transfer ratio h_{FE} vs. collector
- High transition frequency f_T
- A complementary pair with 2SA1535 and 2SA1535A, is optimum for the driver-stage of a 60 W to 100 W output amplifier
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Collector to base voltage	2SC3944	V_{CBO}	150	V
	2SC3944A		180	
Collector to emitter voltage	2SC3944	V_{CEO}	150	V
	2SC3944A		180	
Emitter to base voltage		V_{EBO}	5	V
Peak collector current		I_{CP}	1.5	A
Collector current		I_C	1	A
Collector power dissipation	$T_C = 25^{\circ}\text{C}$	P_C	15	W
	$T_a = 25^{\circ}\text{C}$		2.0	
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^{\circ}\text{C}$

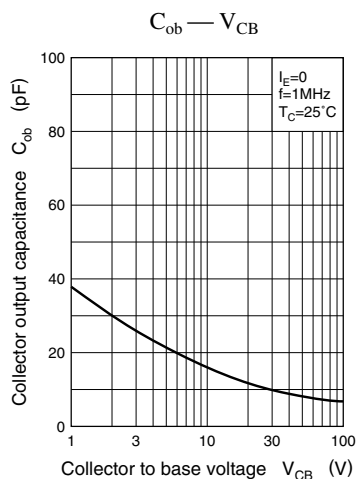
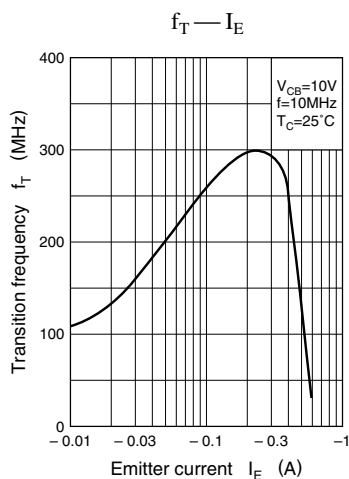
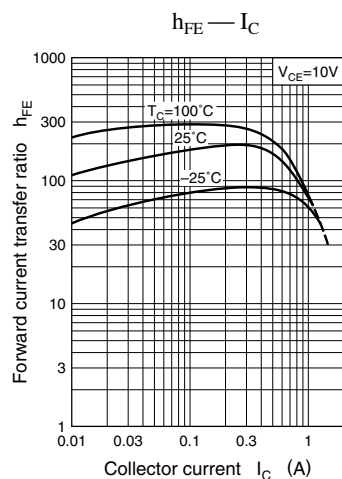
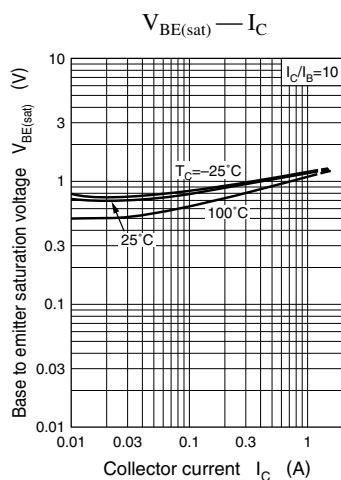
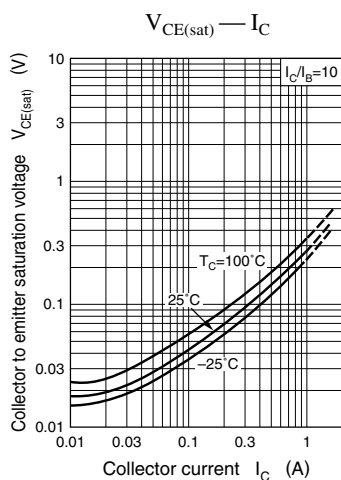
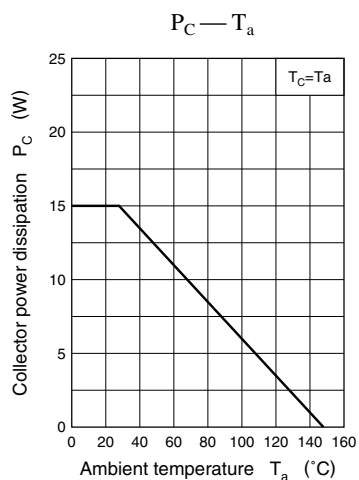


■ Electrical Characteristics $T_C = 25^\circ\text{C}$

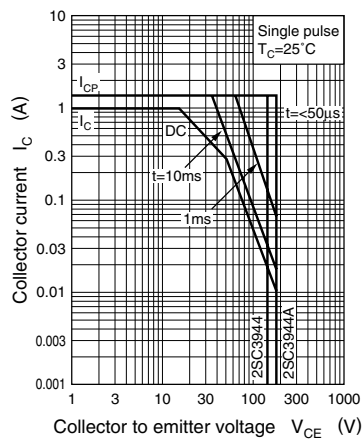
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	2SC3944	I_{CBO}	$V_{CB} = 150\text{ V}, I_E = 0$		10	μA
	2SC3944A		$V_{CB} = 180\text{ V}, I_E = 0$		10	
Collector to base voltage	2SC3944	V_{CEO}	$I_C = 1\text{ mA}, I_B = 0$	150		V
	2SC3944A			180		
Emitter cutoff current	V_{EBO}	$I_E = 10\text{ }\mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio	h_{FE1} *	$V_{CE} = 10\text{ V}, I_C = 150\text{ mA}$	95	160	220	
	h_{FE2}	$V_{CE} = 5\text{ V}, I_C = 500\text{ mA}$	50	100		
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		0.5	2	V
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{ mA}, I_B = 50\text{ mA}$		1	2	V
Transition frequency	f_T	$V_{CB} = 10\text{ V}, I_E = -50\text{ mA}, f = 10\text{ MHz}$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$		30	50	pF

Note) *: Rank classification

Rank	Q	R
h_{FE1}	95 to 155	130 to 220



Area of safe operation (ASO)



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